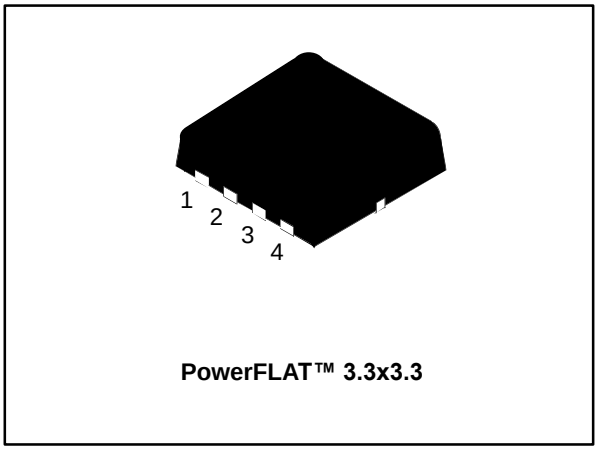
STL8N6F7

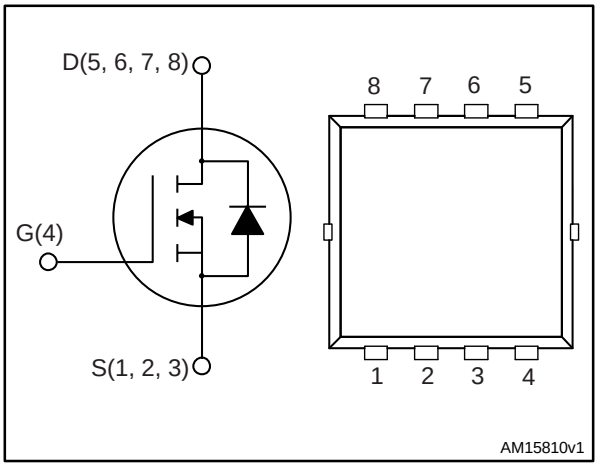
N-channel 60 V, 0.019 Ω typ., 8 A STripFET™ F7 Power MOSFET in a PowerFLAT™ 3.3x3.3 package

Datasheet - production data



PowerFLAT™ 3.3x3.3

Figure 1: Internal schematic diagram



Features

Order code	V_{DS}	$R_{DS(on)}$ max	I_D
STL8N6F7	60 V	0.023 Ω	8 A

- Among the lowest $R_{DS(on)}$ on the market
- Excellent figure of merit (FoM)
- Low C_{rss}/C_{iss} ratio for EMI immunity
- High avalanche ruggedness

Applications

- Switching applications

Description

This N-channel Power MOSFET utilizes STripFET™ F7 technology with an enhanced trench gate structure that results in very low on-state resistance, while also reducing internal capacitance and gate charge for faster and more efficient switching.

Table 1: Device summary

Order code	Marking	Package	Packing
STL8N6F7	8N6F7	PowerFLAT™ 3.3x3.3	Tape and reel

This is information on a product in full production.

Contents

1 Electrical ratings

Table 2: Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage	60	V
V_{GS}	Gate-source voltage	± 20	V
I_D (1)	Drain current (continuous) at T_C = 25 °C	36	A
I_D (1)	Drain current (continuous) at T_C = 100 °C	22	A
I_{DM} (1)(2)	Drain current (pulsed)	144	A
I_D (3)	Drain current (continuous) at T_{pcb} = 25 °C	8	A
I_D (3)	Drain current (continuous) at T_{pcb} = 100 °C	5	A
I_{DM} (2)(3)	Drain current (pulsed)	32	A
P_{TOT} (1)	Total dissipation at T_C = 25 °C	60	W
P_{TOT} (3)	Total dissipation at T_{pcb} = 25 °C	3	W
T_{stg}	Storage temperature	-55 to 150	°C
T_j	Operating junction temperature		

Notes:

(1)This value is rated according to $R_{thj\text{-}c}$.

(2)Pulse width limited by safe operating area.

(3)This value is rated according to $R_{thj\text{-}pcb}$.

Table 3: Thermal data

Symbol	Parameter	Value	Unit
$R_{thj\text{-}pcb}$ (1)	Thermal resistance junction-pcb max.	42.8	°C/W
$R_{thj\text{-}case}$	Thermal resistance junction-case max.	2.1	°C/W

Notes:

(1)When mounted on FR-4 board of 1 inch², 2oz Cu, t < 10 sec.

2 Electrical characteristics

(T_C = 25 °C unless otherwise specified)

Table 4: On /off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	I_D = 1 mA, V_{GS} = 0 V	60			V
I_{DSS}	Zero gate voltage drain current	V_{GS} = 0 V V_{DS} = 60 V			1	µA
I_{GSS}	Gate-body leakage current	V_{GS} = 20 V, V_{DS} = 0 V			100	nA
$V_{GS(th)}$	Gate threshold voltage	V_{DS} = V_{GS}, I_D = 250 µA	2		4	V
$R_{DS(on)}$	Static drain-source on-resistance	V_{GS} = 10 V, I_D = 4 A		0.019	0.023	Ω

Table 5: Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	V_{DS} = 30 V, f = 1 MHz, V_{GS} = 0 V	-	420	-	pF
C_{oss}	Output capacitance		-	215	-	pF
C_{rss}	Reverse transfer capacitance		-	16	-	pF
Q_g	Total gate charge	V_{DD} = 30 V, I_D = 8 A, V_{GS} = 10 V (see *Figure 14: "Test circuit for gate charge behavior"*)	-	8	-	nC
Q_{gs}	Gate-source charge		-	2.3	-	nC
Q_{gd}	Gate-drain charge		-	2.1	-	nC

Table 6: Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	V_{DD} = 30 V, I_D = 4 A, R_G = 4.7 Ω, V_{GS} = 10 V (see *Figure 13: "Test circuit for resistive load switching times"*)	-	7.85	-	ns
t_r	Rise time		-	3.25	-	ns
$t_{d(off)}$	Turn-off delay time		-	12.1	-	ns
t_f	Fall time		-	3.95	-	ns

Table 7: Source-drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
V_{SD} (1)	Forward on voltage	I_{SD} = 8 A, V_{GS} = 0 V	-		1.2	V
t_{rr}	Reverse recovery time	I_D = 8 A, di/dt = 100 A/µs V_{DD} = 48 V (see *Figure 15: "Test circuit for inductive load switching and diode recovery times"*	-	17.1		ns
Q_{rr}	Reverse recovery charge		-	6.67		nC
I_{RRM}	Reverse recovery current		-	0.8		A

Notes:

(1)Pulsed: pulse duration = 300 µs, duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 2: Safe operating area

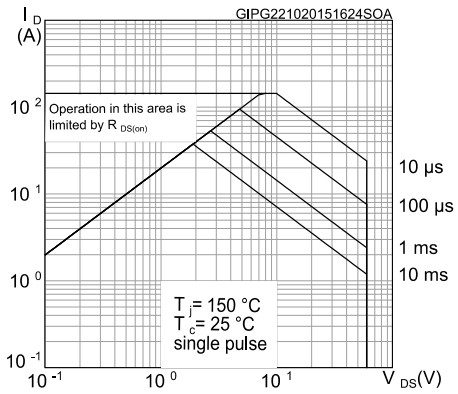


Figure 3: Thermal impedance

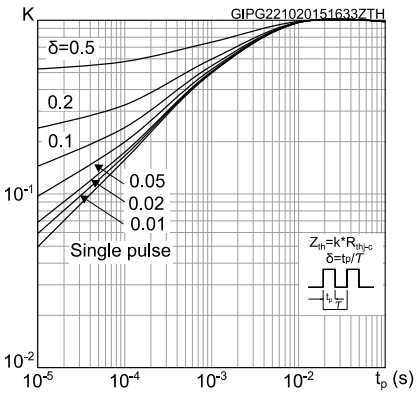


Figure 4: Output characteristics

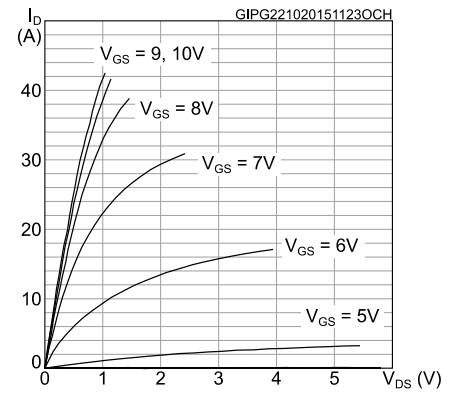


Figure 5: Transfer characteristics

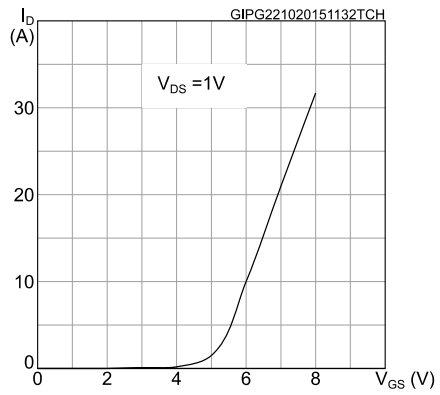


Figure 6: Gate charge vs gate-source voltage

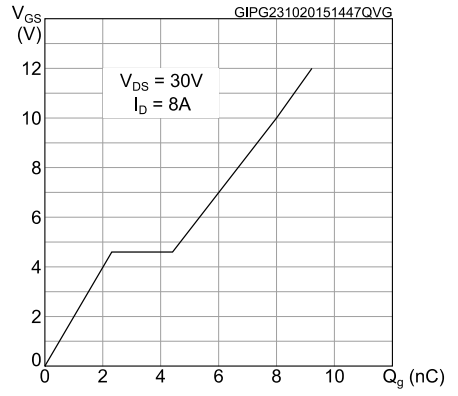


Figure 7: Static drain-source on-resistance

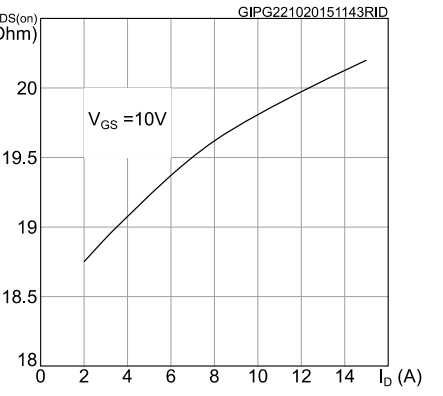


Figure 8: Capacitance variations

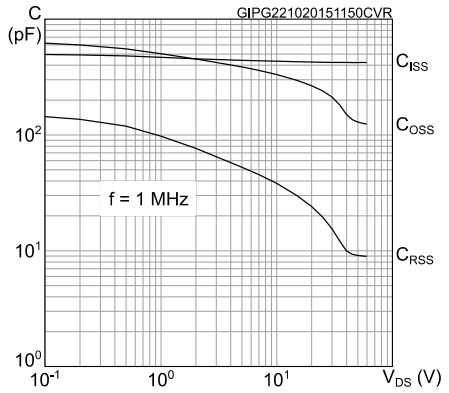


Figure 9: Normalized gate threshold voltage vs temperature

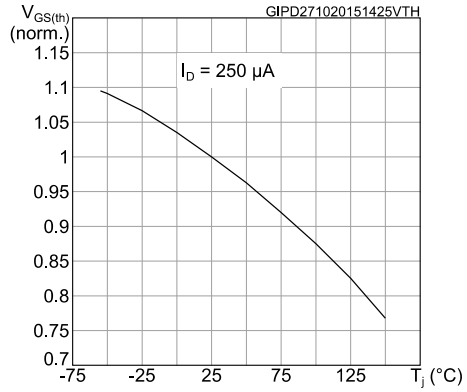


Figure 10: Normalized on-resistance vs temperature

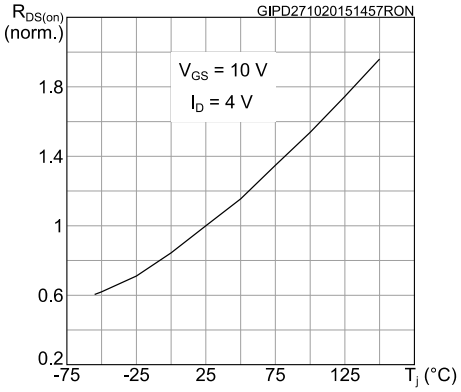


Figure 11: Normalized V(BR)DSS vs temperature

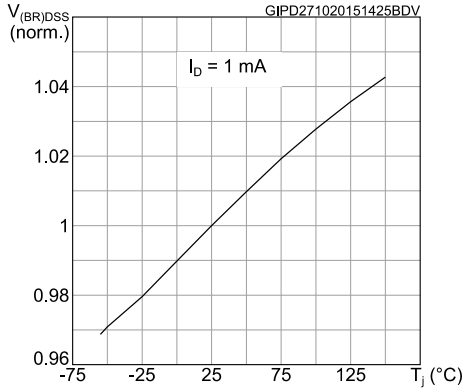
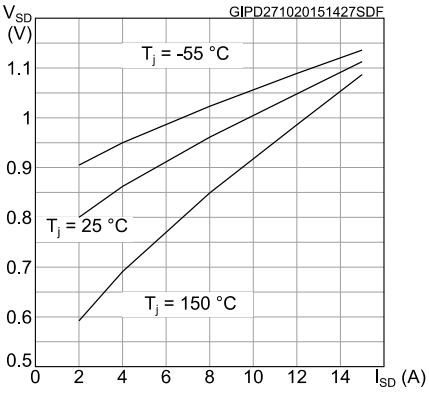


Figure 12: Source-drain diode forward characteristics



3 Test circuits

Figure 13: Test circuit for resistive load switching times

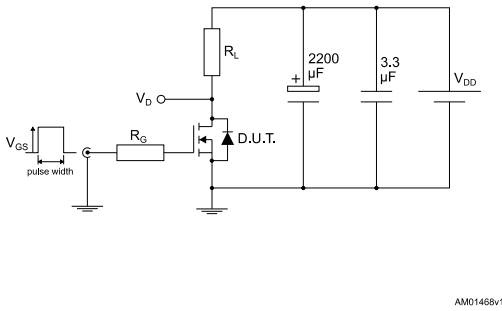


Figure 14: Test circuit for gate charge behavior

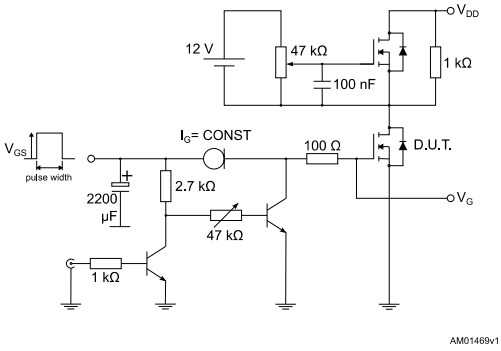


Figure 15: Test circuit for inductive load switching and diode recovery times

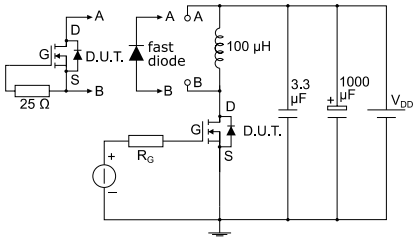


Figure 16: Unclamped inductive load test circuit

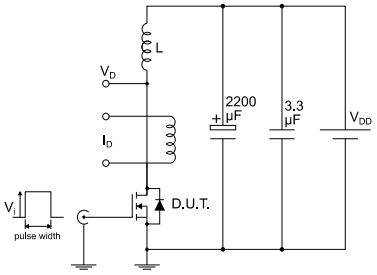


Figure 17: Unclamped inductive waveform

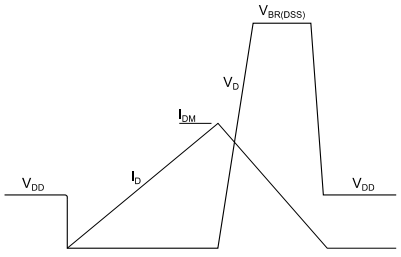
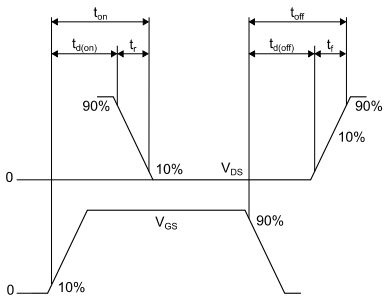


Figure 18: Switching time waveform



4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: ***www.st.com***. ECOPACK® is an ST trademark.

4.1 PowerFLAT 3.3x3.3 package information

Figure 19: PowerFLAT™ 3.3x3.3 package outline

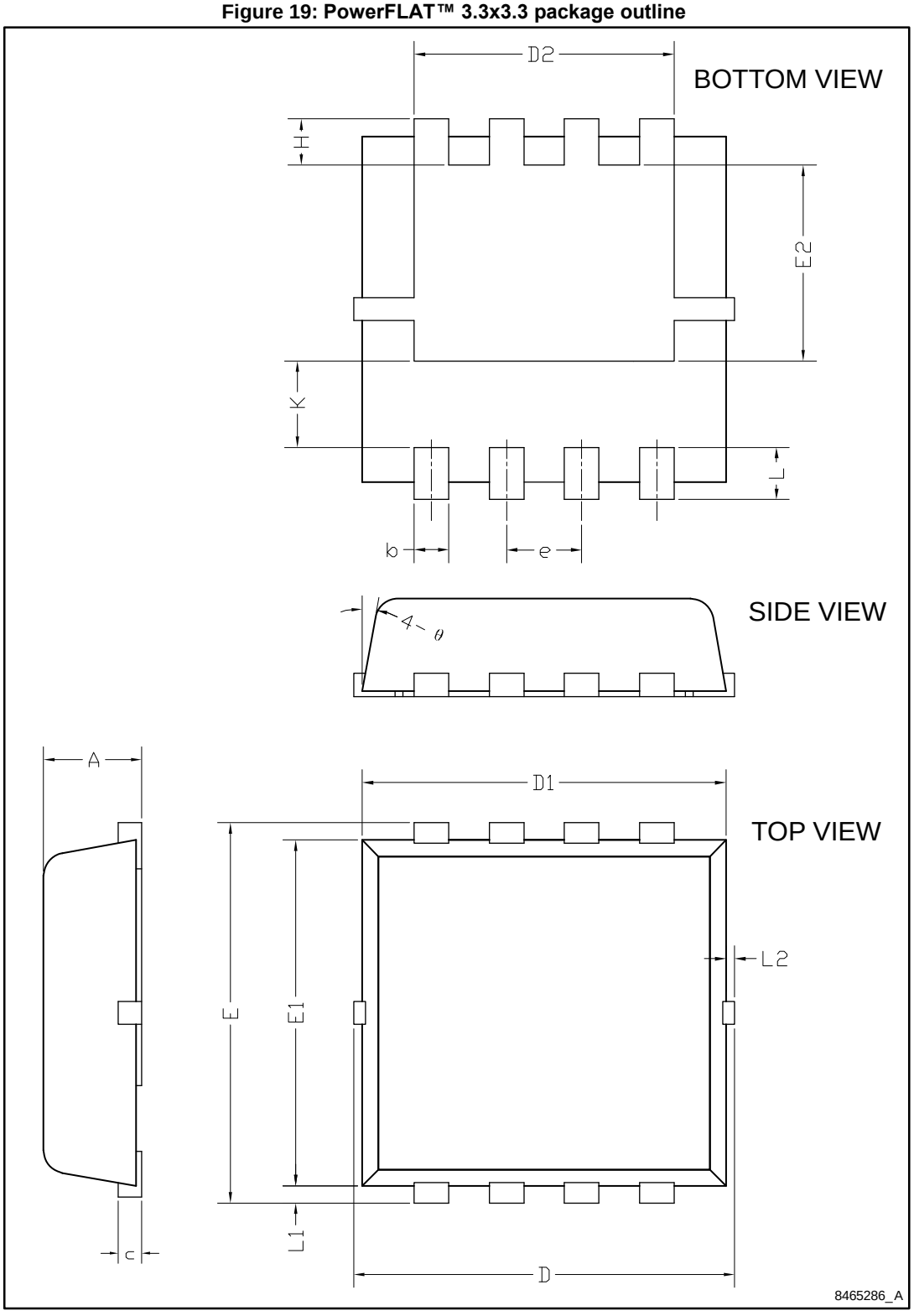
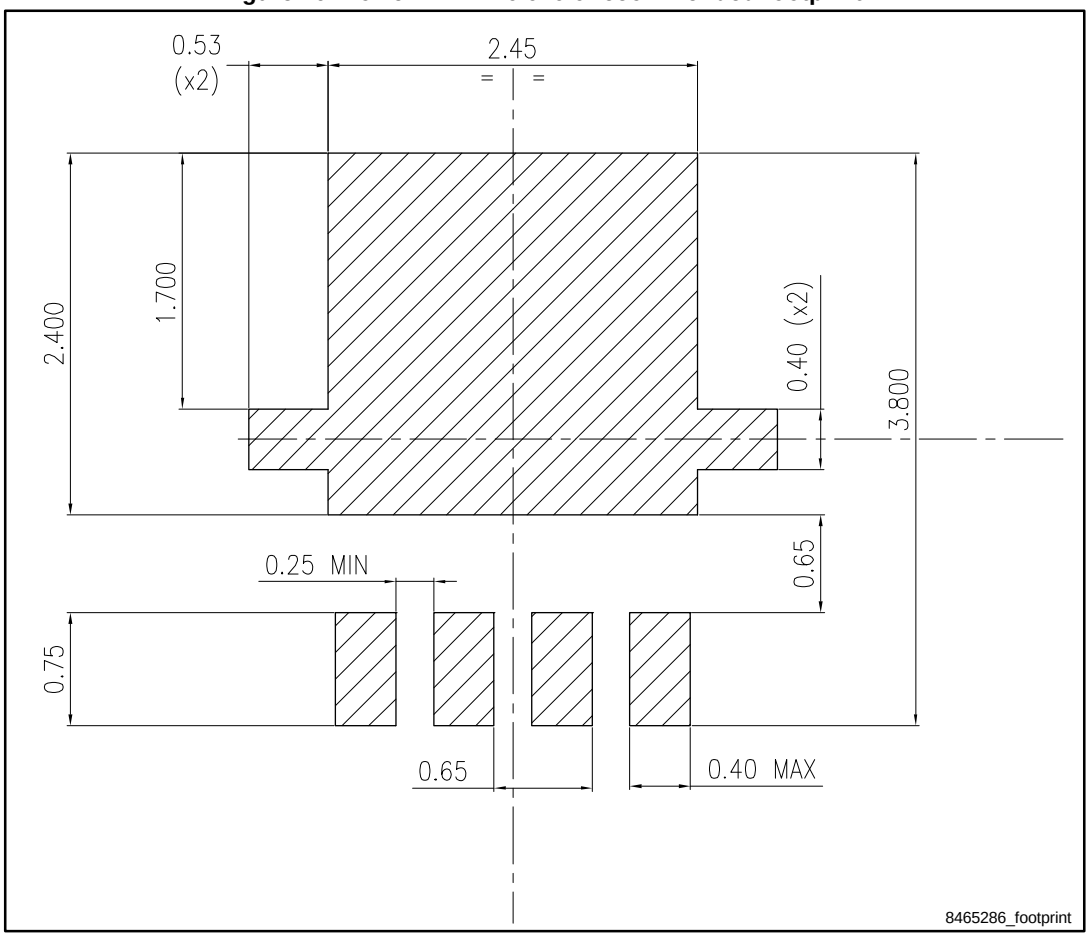


Table 8: PowerFLAT™ 3.3x3.3 package mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	0.70	0.80	0.90
b	0.25	0.30	0.39
c	0.14	0.15	0.20
D	3.10	3.30	3.50
D1	3.05	3.15	3.25
D2	2.15	2.25	2.35
e	0.55	0.65	0.75
E	3.10	3.30	3.50
E1	2.90	3.00	3.10
E2	1.60	1.70	1.80
H	0.25	0.40	0.55
K	0.65	0.75	0.85
L	030	0.45	0.60
L1	0.05	0.15	0.25
L2			0.15
θ	8°	10°	12°

Figure 20: PowerFLAT™ 3.3x3.3 recommended footprint



5 Revision history

Table 9: Document revision history

Date	Revision	Changes
20-Aug-2015	1	First release.
22-Oct-2015	2	Updated title and features in cover page. Updated *Table 4: "On /off states"*, *Table 5: "Dynamic"*, *Table 6: "Switching times"* and *Table 7: "Source-drain diode"*. Added *Section 3.1: "Electrical characteristics (curves)"*. Document status promoted from preliminary di production data.

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